NSN 5962-01-264-3005

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View Online at https://aerobasegroup.com/nsn/5962-01-264-3005

Body Length:	
0.358 inches	
Body Width:	
0.358 inches	
Body Height:	
0.100 inches	
Maximum Power Diss	ipation Rating:
2.0 watts	
Operating Tempuratu	re Range:
-55.0/+125.0 degrees c	elsius
Storage Tempurature	Range:
-65.0/+150.0 degrees c	elsius
Features Provided:	
Hermetically sealed an	d burn in and programmable and positive outputs
Inclosure Material:	
Ceramic and glass	
Inclosure Configuration	on:
Leadless flat pack	
Output Logic Form:	
Transistor-transistor log	jic
Input Circuit Pattern:	
16 input	
Case Outline Source	And Designator:
C-2 mil-m-38510	
Current Rating Per Ch	aracteristic:
_	ward current, peak total value not applicable
Terminal Surface Trea	
Solder	
Voltage Rating And T	ype Per Characteristic:
	e and 7.0 volts power source
Time Rating Per Chac	
-	opagation delay time, low to high level output and 45.00 nanoseconds propagation delay time, high to low level
output	
Memory Device Type:	
Pal	
Test Data Document:	
	dard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Qu	
20 leadless	
Shelf Life:	
N/a	
Unit Of Measure:	

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Demilitarization:

No

Fiig:

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